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from 1mm to several tens of mm, and the thickness of the semiconductor substrate ranges from 30 μ m to 150 μ m. A ground conductor (not shown) such as Au is formed on the back or reverse side of the semiconductor substrate 12. Reference numerals 14 indicate transistors placed on the semiconductor substrate 12. In the present embodiment, FETs are used as the transistors. Reference numeral 16 indicates a distribution circuit, i.e., a divider circuit, placed on the semiconductor substrate 12. Reference numeral 16a indicates a branch portion of the distribution circuit 16. Reference numerals 16b indicate a plurality of first lines which branch off from the branch portion 16a of the distribution circuit 16. In the present embodiment, the two branch off from the branch portion 16a. Reference numerals 16c indicate impedance converter circuits which constitute the first lines 16b respectively. They are, for example, low-impedance microstrip lines, i.e., microstrip lines each having a $\lambda/4$ electrical length.

Reference numeral 18 indicates a composite or synthetic circuit, i.e., a combiner circuit, placed in the semiconductor substrate 12. Reference numeral 18a indicates a confluent or combined portion of the synthetic circuit 18. Reference numerals 18b indicate second lines constituting branch lines, which join the combined portion 18a of the synthetic circuit 18. Reference numerals 18c indicate impedance converter circuits which constitute the second lines 18b respectively. They are, for example, low-impedance microstrip lines, i.e., microstrip lines each having a $\lambda/4$ electrical length.

IN THE CLAIMS:

Please cancel claim 3.

Claims 1, 4 and 5 have been amended to read as follows:

- KA 10
1. (Amended) A high-frequency circuit device comprising: